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APPLICATION NO. FILING DATE  10/767,292 01/29/2004		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO. 4993	
		Hai Cong	CS03-016		
7590 05/20/2005			EXAMINER		
STEPHEN B.	<del>-</del>	GURLEY, LYNNE ANN			
28 DAVIS AVI POUGHKEEPS	ENUE SIE, NY 12603		ART UNIT	PAPER NUMBER	
	,		2812		
			DATE MAILED: 05/20/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

			NI	A				
		Applicati	on No.	Applicant(s)	$\langle \omega \rangle$			
	Office Action Commons	10/767,2	92	CONG ET AL.				
	Office Action Summary	Examine	r	Art Unit				
		Lynne A.		2812				
Period fo	The MAILING DATE of this community or Reply	nication appears on th	e cover sheet with	n the correspondence addr	9SS			
THE - Exte after - If the - If NO - Failt Any	IORTENED STATUTORY PERIOD I MAILING DATE OF THIS COMMUN ensions of time may be available under the provision of SIX (6) MONTHS from the mailing date of this come e period for reply specified above is less than thirty (5) operiod for reply is specified above, the maximum sure to reply within the set or extended period for repl reply received by the Office later than three months and patent term adjustment. See 37 CFR 1.704(b).	NICATION. as of 37 CFR 1.136(a). In no eventuring the standard of the standard will apply and will will, by statutory period will apply and will will, by statute, cause the apply and will will, by statute, cause the apply and will will, by statute, cause the apply and will, will, by statute, cause the apply and will, will, by statute, cause the apply and will apply apply and will apply and will apply apply and will apply appl	vent, however, may a rep tutory minimum of thirty vill expire SIX (6) MONTI olication to become ABA	oly be timely filed  (30) days will be considered timely.  HS from the mailing date of this commoder.  NDONED (35 U.S.C. § 133).	munication.			
Status								
1)⊠	Responsive to communication(s) fil	led on <i>08 February 20</i>	<u>005</u> .					
•	This action is FINAL.	2b) ☐ This action is r						
3)□								
Disposit	ion of Claims							
5)□ 6)⊠ 7)□	Claim(s) <u>1-30</u> is/are pending in the 4a) Of the above claim(s) is/claim(s) is/are allowed. Claim(s) <u>1-30</u> is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restr	are withdrawn from co						
Applicat	tion Papers							
•	The specification is objected to by t							
10)□	The drawing(s) filed on is/are							
	Applicant may not request that any obj		-					
11)	Replacement drawing sheet(s) includir The oath or declaration is objected	•	= *	•				
Priority	under 35 U.S.C. § 119							
a)	Acknowledgment is made of a claim All b) Some * c) None of:  1. Certified copies of the priority 2. Certified copies of the priority 3. Copies of the certified copies application from the Internation	y documents have been y documents have been sof the priority documental Bureau (PCT Ru	en received. en received in Ap ents have been r le 17.2(a)).	plication No eceived in this National St	tage			
	See the attached detailed Office acti	ion for a list of the cen	uneu wpies not n	years. She	rley			
				LYNNE A. GURLEY	1			
Attachmer	nt(s)			PRIMARY PATENT EXA TC 2800, AU 2812	AMINER			
_	ce of References Cited (PTO-892)		4) Interview Su	mmary (PTO-413)				
2)	ce of Draftsperson's Patent Drawing Review ( rmation Disclosure Statement(s) (PTO-1449 o er No(s)/Mail Date		Paper No(s)	/Mail Date ormal Patent Application (PTO-1	52)			

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## **DETAILED ACTION**

This Office Action is in response to the amendment filed 2/8/05.

Currently, claims 1-32 are pending. Claims 31-32 have been canceled.

## Specification

1. The lengthy specification has not been checked to the extent necessary to determine the presence of all possible minor errors. Applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

## Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. The factual inquiries set forth in *Graham* v. *John Deere Co.*, 383 U.S. 1, 148 USPQ 459 (1966), that are applied for establishing a background for determining obviousness under 35 U.S.C. 103(a) are summarized as follows:
  - 1. Determining the scope and contents of the prior art.
  - 2. Ascertaining the differences between the prior art and the claims at issue.
  - 3. Resolving the level of ordinary skill in the pertinent art.
  - 4. Considering objective evidence present in the application indicating obviousness or nonobviousness.
- 4. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various

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claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

5. Claims 1-30 are rejected under 35 U.S.C. 103(a) as being unpatentable over Weidman et al. (US 2003/0176058, dated 9/18/03, field 3/18/02).

Weidman shows the method as claimed in figures 1A-1H and corresponding text, with substrate 2 including insulating layer 6 with embedded conductor 4, IMD 16, hard masks 20 and 22, via opening 32 with photoresist 42 and BARC 40. The hard mask and IMD layers are patterned and etched to form open via and trench openings (figs. 1E-1H) for subsequent conducting metal fill. [0009] shows that the hard mask layers are formed of undoped SiC or SiN.

Weidman lacks anticipation only in not explicitly teaching that the BARC is formed with photoresist and that the via is filled with photoresist; the thicknesses of layers, and some materials of the IMD/hard mask stack, the etching formula, repeating the steps to form multiple layers of interconnect, cu seed layer in the trench and via openings, forming excess copper metal over the copper seed layer and then planarizing the excess copper, and, MOSFET CMOS memory and logic devices.

It would have been obvious to one of ordinary skill in the art to have had formed the BARC layer of photoresist and to have filled the via openings with photoresist, in the method of

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Weidman, with the motivation that treated or specific types of photoresist are conventionally used as BARC layers and photoresist has also been commonly used to fill a via to facilitate patterning of an opening, especially of the damascene type in an insulating stack. The used of photoresist as a BARC film and to fill the via would make the process more efficient in that less materials would have to be used.

It would have been obvious to one of ordinary skill in the art to have had the claimed ranges of thicknesses of layers, and the claimed materials of the IMD/hard mask stack, the etching formula, to have repeated the steps to form multiple layers of interconnect, to have had a cu seed layer in the trench and via openings, to have formed excess copper metal over the copper seed layer and then planarized the excess copper, and, to have had MOSFET CMOS memory and logic devices, in the method of Weidman, with the motivation that these parameters are within the scope of conventional processing parameters and well know to those of ordinary skill in the art. The cu seed layers and planarization of excess cu are also well known processing steps for cu interconnect technology. Additionally, the inclusion of MOSFET CMOS memory and logic devices in the substrate beneath the interconnect is conventional as well and obvious to one of ordinary skill in the art.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lynne A. Gurley whose telephone number is 571-272-1670. The examiner can normally be reached on M-F 7:30-4:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Lebentritt can be reached on 571-272-1873. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Lynne A. Gurley

Primary Patent Examiner TC 2800, Art Unit 2812

LAG

May 16, 2005